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ประวัติผู้เขียนวิทยานิพนธ์

นายมตินนท์ ไมตรีบริรักษ์ เกิดเมื่อวันที่ 6 กุมภาพันธ์ พุทธศักราช 2528 อาศัยอยู่บ้านเลขที่ 211/46 ถนนนนทรี แขวงช่องนนทรี เขตยานนาวา กรุงเทพมหานคร จบการศึกษาระดับมัธยมศึกษาจากโรงเรียนบดินทรเดชา (สิงห์ สิงหเสนี) ปีการศึกษา 2545 และจบการศึกษาระดับอุดมศึกษา ปริญญาวิศวกรรมศาสตรบัณฑิต สาขาวิศวกรรมไฟฟ้า จาก จุฬาลงกรณ์มหาวิทยาลัย ปีการศึกษา 2549